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Docket: 0756-7218

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re DIVISIONAL application of)
Shunpei YAMAZAKI et al.)
Based on Serial No. 10/214,691) Group Art Unit: 2826
Filed: August 9, 2002) Examiner: Abraham
For: SEMICONDUCTOR DEVICE AND)
METHOD OF FABRICATING SAME)

INFORMATION DISCLOSURE STATEMENT

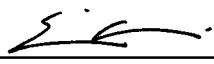
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 10/214,691 and predecessor Application Serial No. 08/785,486 and copies of the references can be found in those applications.

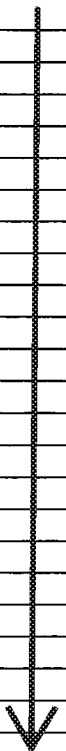
Respectfully submitted,


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Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham Benjamin T Liu
Sheet	1	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/		5,686,328		Zhang et al.	11/11/97	
		5,763,899		Yamazaki et al.	06/09/98	
		5,782,665		Weisfield et al.	07/21/98	
		5,922,125		Zhang	07/13/99	
		6,083,801		Ohtani	07/04/00	
		5,744,822		Takayama et al.	04/28/98	
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		5,766,977		Yamazaki	06/16/98	
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		6,121,683		Yamazaki et al.	09/19/00	
	6,207,969 B1		Yamazaki et al.	03/27/01		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
/BTL/		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.	
↓		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995	

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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/BTL/		5,811,327		Funai et al.	09/22/98	
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		5,821,138		Yamazaki et al.	10/13/98	
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		6,175,348		Zhang et al.	01/16/01	
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		4,534,820		Mori et al.	08/13/85	
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/BTL/		JP	07-335900	Teramoto Satoshi	12/22/95	Abst.
/BTL/		JP	64-081324		03/27/89	Abst.
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/BTL/		IBM Technical Disclosure Bulletin, Vol. 11, No.7, A.R. Baker, Jr.				

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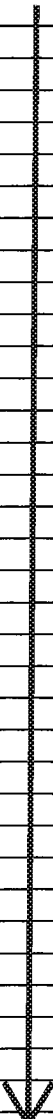
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/BTL/		4,546,376		Nakata et al.	10/08/85	
		4,597,160		Ipri	07/01/86	
		4,634,473		Swartz et al.	01/06/87	
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/BTL/		5,470,763		Hamada	11/28/95	
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7BTL		6,013,929		Ohtani	01/11/00	
		6,048,758		Yamazaki et al.	04/11/00	
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/BTL/		EP	0 178 447			10/09/84		English
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		JP	01-187874			07/27/89		Abst.
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		Green et al., "Method to Purify Semiconductor Wafers," October 1973, pp. 1612-1613, IBM Tech. Discl. Bulletin, Vol. 16, No. 5	
		Boyd, et al., "Oxidation of Silicon Surfaces by CO2 Lasers," July 15, 1982, pp. 162-164, Applied Phys. Letters, Vol. 41, No. 2	
		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 215-216, Lattice Press	

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	Based on 10/214,691
		Filing Date	August 9, 2002
		First Named Inventor	Shunpei YAMAZAKI, et al.
		Group Art Unit	2826
		Examiner Name	Peterson Abraham Benjamin T Liu
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		Attorney Docket Number	0756-7218

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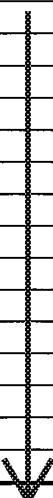
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/BTL/		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990).	

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